

# MS1451

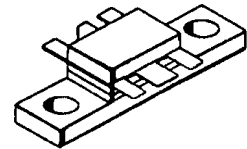
## RF & MICROWAVE TRANSISTORS 800-960 MHz BASE STATION APPLICATIONS

### Features

- 800-960 MHz
- 24 VOLTS
- CLASS AB LINEAR OPERATION
- $P_{OUT} = 15$  WATTS
- $G_P = 8.0$  dB MINIMUM
- COMMON EMITTER CONFIGURATION

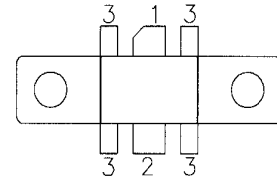
### DESCRIPTION:

The MS1451 is a gold metallized silicon NPN planar transistor designed for high linearity Class AB operation in cellular base station applications. The MS1451 is designed as a medium power output device or as the driver for MS1452. Diffused emitter ballast resistors provide thermal stability and reliability under Class AB linear operation.



.230 6LFL (M142)  
epoxy sealed

### PIN CONNECTION



1. Collector      3. Base  
2. Emitter

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	48	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CES</sub>	Collector-Emitter Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V
P <sub>DISS</sub>	Power Dissipation	29	W
I <sub>C</sub>	Device Current	2.5	A
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

### Thermal Data

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	6.0	°C/W
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## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV <sub>cbo</sub>	I <sub>C</sub> = 50 mA	I <sub>E</sub> = 0 mA	48	---	---	V
BV <sub>ceo</sub>	I <sub>C</sub> = 20 mA	I <sub>B</sub> = 0 mA	25	---	---	V
BV <sub>ebo</sub>	I <sub>E</sub> = 5 mA	I <sub>C</sub> = 0 mA	3.5	---	---	V
I <sub>cbo</sub>	V <sub>CB</sub> = 24 V	I <sub>E</sub> = 0 mA	---	---	1.0	mA
H <sub>FE</sub>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 100mA	20	---	100	---

### DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P <sub>OUT</sub>	f = 960 MHz	P <sub>IN</sub> = 2.4W	V <sub>CC</sub> = 24V	15	---	---	W
G <sub>P</sub>	f = 960 MHz	P <sub>IN</sub> = 2.4W	V <sub>CC</sub> = 24V	8	---	---	dB
η <sub>C</sub>	f = 960 MHz	P <sub>IN</sub> = 2.4 W	V <sub>CC</sub> = 24V	45	---	---	%
C <sub>ob</sub>	f = 1 MHz	V <sub>CB</sub> = 24V		---	---	24	pf

Conditions: V<sub>CC</sub> = 24 V IC<sub>Q</sub> = 75 mA

### IMPEDANCE DATA

FREQ	Z <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)
900 MHz	1.3 + j1.98	4.0 + j5.5
930 MHz	1.42 + j2.3	3.18 + j5.0
960 MHz	1.45 + j2.62	2.96 + j4.07

P<sub>OUT</sub> = 15W

V<sub>CE</sub> = 24V

I<sub>CQ</sub> = 75mA

**PACKAGE MECHANICAL DATA**

